SIHS36N50D-E3 Datasheet

https://www.DiGi-Electronics.com

DiGi Electronics Part Number	SIHS36N50D-E3-DG
Manufacturer	Vishay Siliconix
Manufacturer Product Number	SIHS36N50D-E3
Description	MOSFET N-CH 500V 36A SUPER-247
Detailed Description	N-Channel 500 V 36A (Tc) 446W (Tc) Through Hole SUPER-247™ (TO-274AA)

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

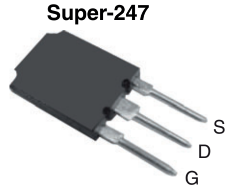
Manufacturer Product Number:	Manufacturer:
SIHS36N50D-E3	Vishay Siliconix
Series:	Product Status:
-	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
500 V	36A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
10V	130mOhm @ 18A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
5V @ 250μA	125 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±30V	3233 pF @ 100 V
FET Feature:	Power Dissipation (Max):
-	446W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Through Hole
Supplier Device Package:	Package / Case:
SUPER-247™ (TO-274AA)	TO-274AA
Base Product Number:	
SIHS36	

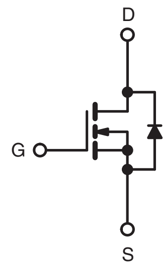
Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
ECCN:	HTSUS:
EAR99	8541.29.0095

D Series Power MOSFET

Super-247





N-Channel MOSFET

FEATURES

- Optimal design
  - Low area specific on-resistance
  - Low input capacitance (C_{iss})
  - Reduced capacitive switching losses
  - High body diode ruggedness
  - Avalanche energy rated (U_{IS})
- Optimal efficiency and operation
  - Low cost
  - Simple gate drive circuitry
  - Low figure-of-merit (FOM): R_{on} x Q_g
  - Fast switching
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Pb-free
RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Consumer electronics
  - Displays (LCD or Plasma TV
- Server and telecom power supplies
  - SMPS
- Industrial
  - Welding, induction heating, motor drives
- Battery chargers

PRODUCT SUMMARY		
V_{DS} (V) at T_J max.	550	
$R_{DS(on)}$ max. at 25 °C (Ω)	V_{GS} = 10 V	0.130
Q_g max. (nC)	125	
Q_{gs} (nC)	23	
Q_{gd} (nC)	37	
Configuration	Single	

ORDERING INFORMATION	
Package	Super-247
Lead (Pb)-free and halogen-free	SiHS36N50D-GE3

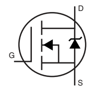
ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V_{DS}	500	V
Gate-source voltage			V_{GS}	± 30	
Gate-source voltage AC (f > 1 Hz)				30	
Continuous drain current (T_J = 150 °C)	V_{GS} at 10 V	T_C = 25 °C	I_D	36	A
		T_C = 100 °C		23	
Pulsed drain current [a]			I_{DM}	112	
Linear derating factor				3.6	W/°C
Single pulse avalanche energy [b]			E_{AS}	332	mJ
Maximum power dissipation			P_D	446	W
Operating junction and storage temperature range			T_J, T_{stg}	- 55 to + 150	°C
Drain-source voltage slope	T_J = 125 °C		dV/dt	24	V/ns
Reverse diode dV/dt [d]				0.1	
Soldering recommendations (peak temperature)	for 10 s			300 [c]	°C

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature
b. V_{DD} = 50 V, starting T_J = 25 °C, L = 2.3 mH, R_g = 25 Ω, I_{AS} = 17 A
c. 1.6 mm from case
d. $I_{SD} \leq I_D$, starting T_J = 25 °C

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum junction-to-ambient	R_{thJA}	-	40	°C/W
Maximum junction-to-case (drain)	R_{thJC}	-	0.28	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA	500	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 250 μA	-	0.52	-	V/°C
Gate threshold voltage (N)	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	3.0	-	5.0	V
Gate-source leakage	I_{GSS}	V_{GS} = ± 30 V	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = 500 V, V_{GS} = 0 V	-	-	1	μA
		V_{DS} = 400 V, V_{GS} = 0 V, T_J = 125 °C	-	-	10	
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 18 A	-	0.105	0.130	Ω
Forward transconductance [a]	g_{fs}	V_{DS} = 50 V, I_D = 18 A	-	12.8	-	S
Dynamic						
Input capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 100 V, f = 1 MHz	-	3233	-	pF
Output capacitance	C_{oss}		-	285	-	
Reverse transfer capacitance	C_{rss}		-	25	-	
Effective output capacitance, energy related [a]	$C_{o(er)}$	V_{GS} = 0 V, V_{DS} = 0 V to 400 V	-	240	-	
Effective output capacitance, time related [b]	$C_{o(tr)}$		-	352	-	
Total gate charge	Q_g	V_{GS} = 10 V, I_D = 18 A, V_{DS} = 400 V	-	83	125	nC
Gate-source charge	Q_{gs}		-	23	-	
Gate-drain charge	Q_{gd}		-	37	-	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 400 V, I_D = 18 A, V_{GS} = 10 V, R_g = 9.1 Ω	-	33	66	ns
Rise time	t_r		-	89	134	
Turn-off delay time	$t_{d(off)}$		-	79	119	
Fall time	t_f		-	68	102	
Gate input resistance	R_g	f = 1 MHz, open drain	-	1.8	-	Ω
Drain-source body diode characteristics						
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	36	A
Pulsed diode forward current	I_{SM}		-	-	144	
Diode forward voltage	V_{SD}	T_J = 25 °C, I_S = 18 A, V_{GS} = 0 V	-	-	1.2	V
Reverse recovery time	t_{rr}	T_J = 25 °C, I_F = I_S = 18 A, dI/dt = 100 A/μs, V_R = 20 V	-	490	-	ns
Reverse recovery charge	Q_{rr}		-	8.2	-	μC
Reverse recovery current	I_{RRM}		-	31	-	A

Notes

a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

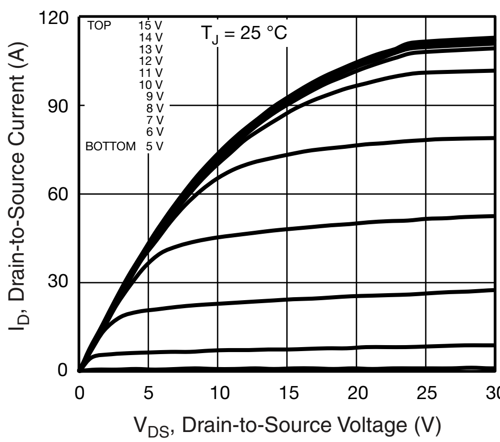


Fig. 1 - Typical Output Characteristics

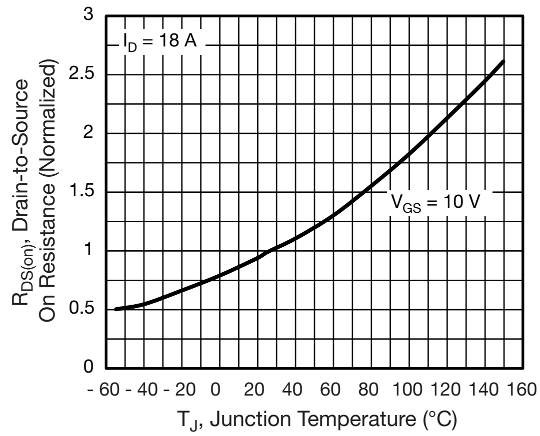


Fig. 4 - Normalized On-Resistance vs. Temperature

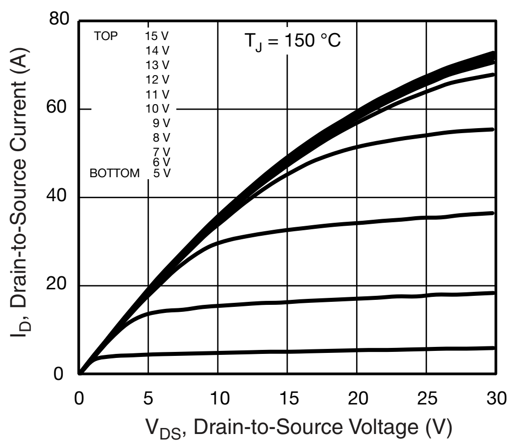


Fig. 2 - Typical Output Characteristics

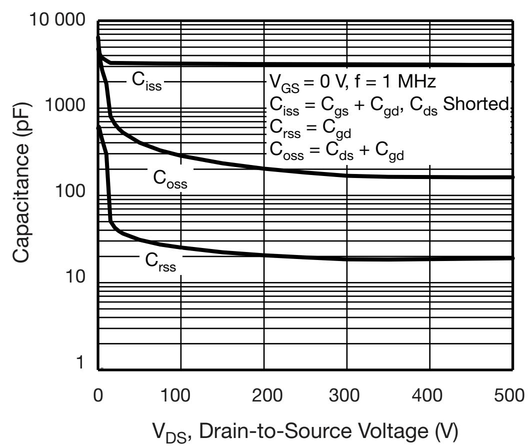


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

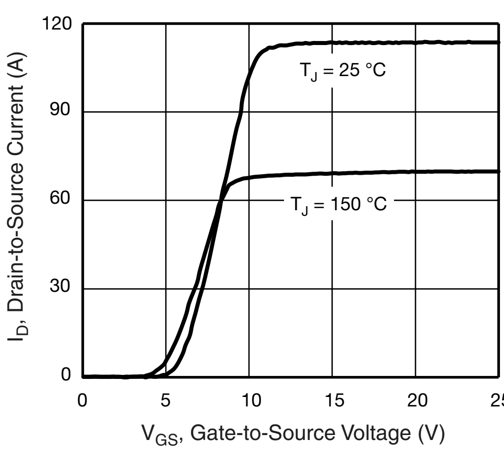


Fig. 3 - Typical Transfer Characteristics

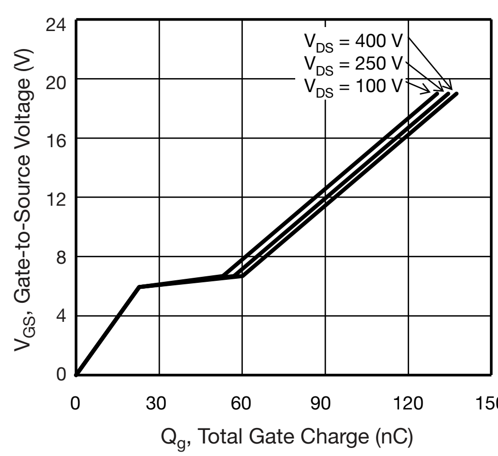


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

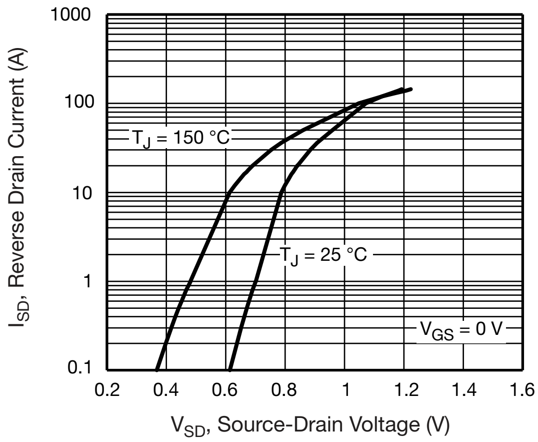


Fig. 7 - Typical Source-Drain Diode Forward Voltage

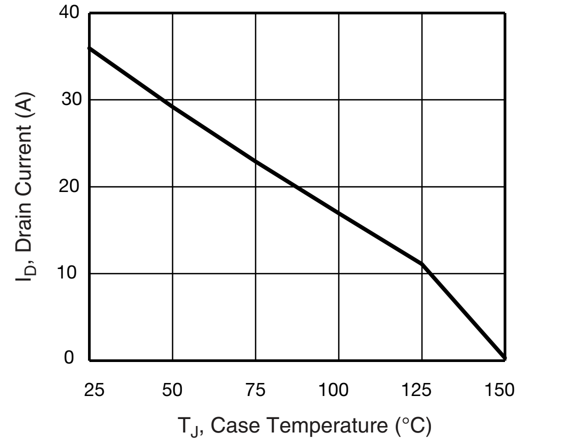
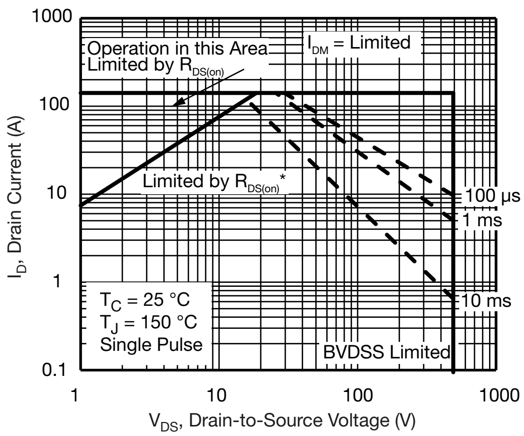


Fig. 9 - Maximum Drain Current vs. Case Temperature



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Fig. 8 - Maximum Safe Operating Area

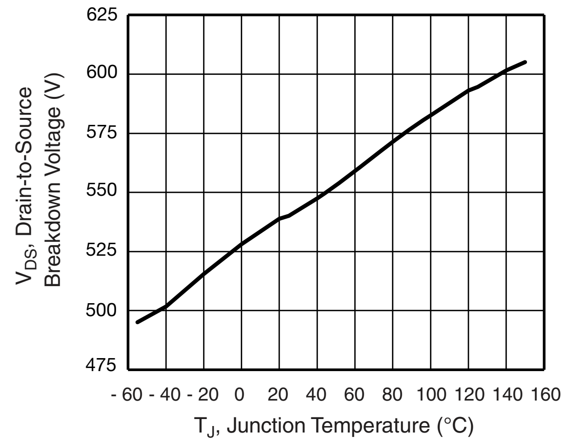


Fig. 10 - Temperature vs. Drain-to-Source Voltage

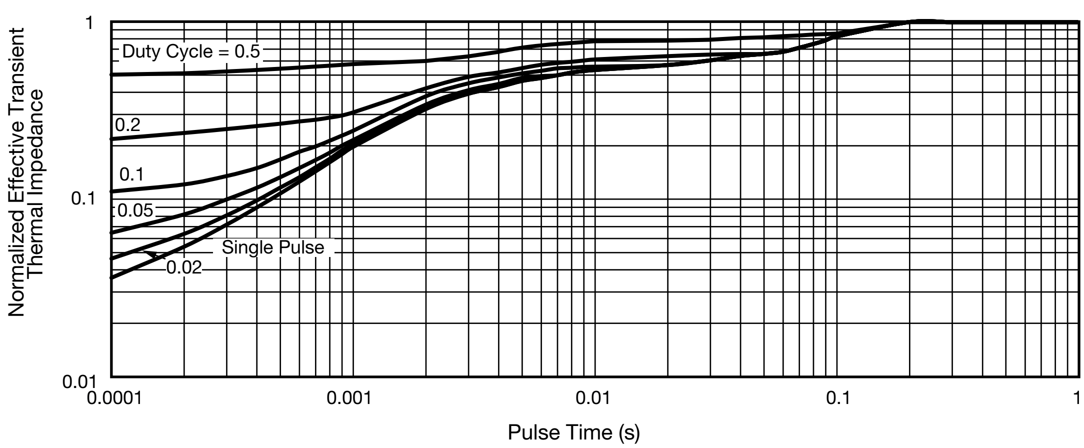


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

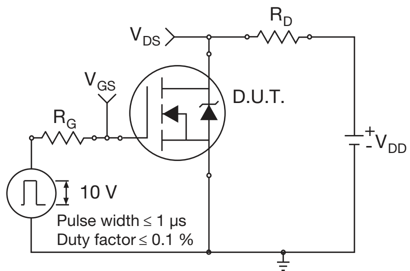


Fig. 12 - Switching Time Test Circuit

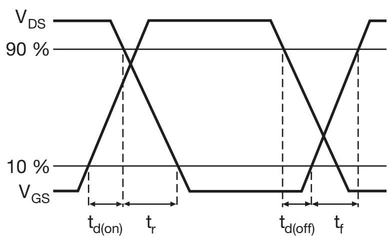


Fig. 13 - Switching Time Waveforms

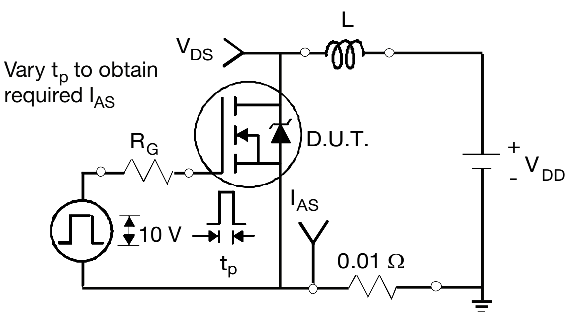


Fig. 14 - Unclamped Inductive Test Circuit

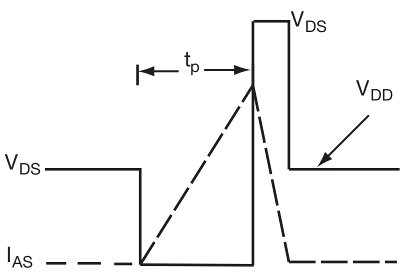


Fig. 15 - Unclamped Inductive Waveforms

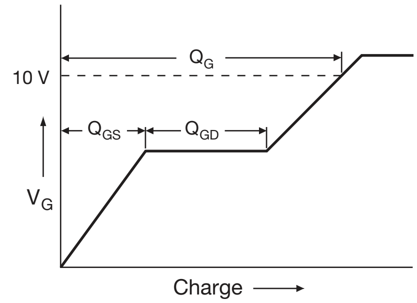


Fig. 16 - Basic Gate Charge Waveform

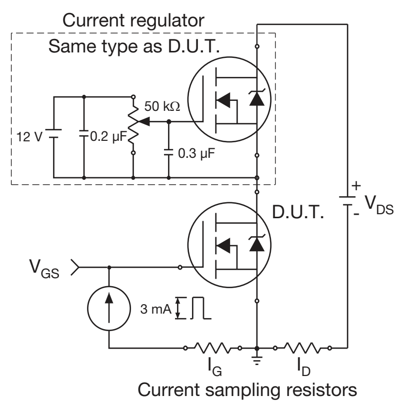
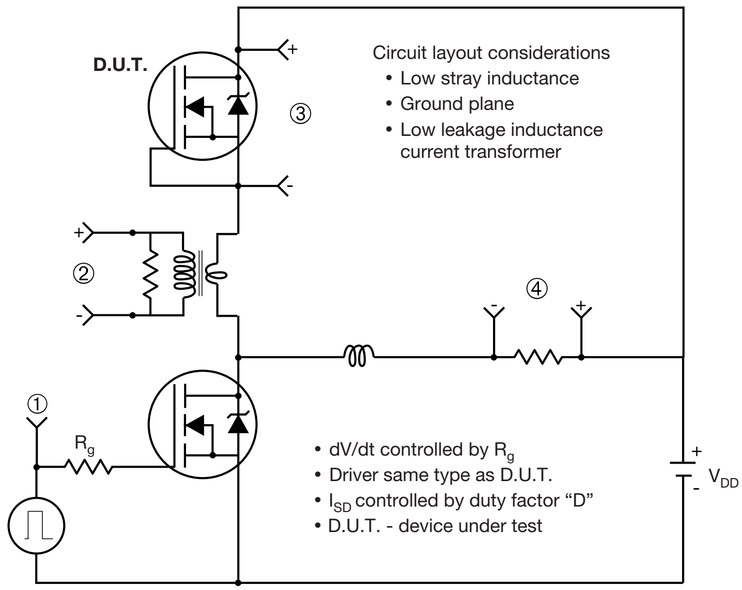
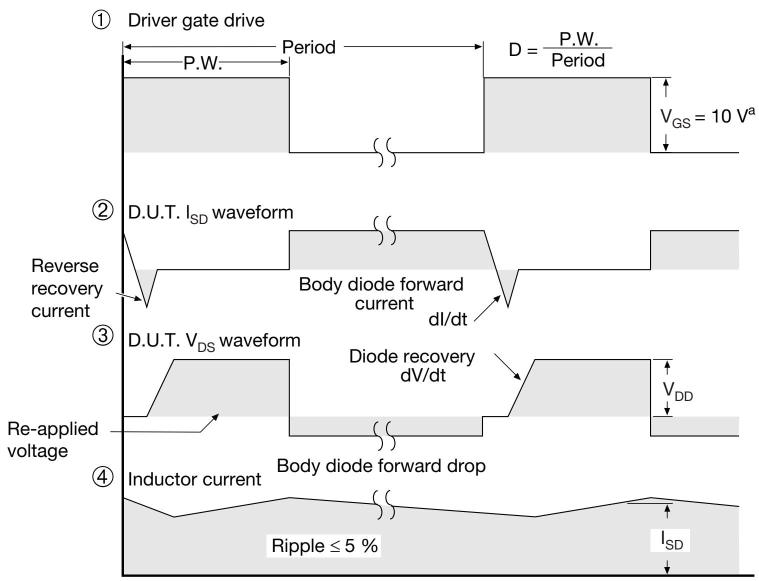


Fig. 17 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit





Note

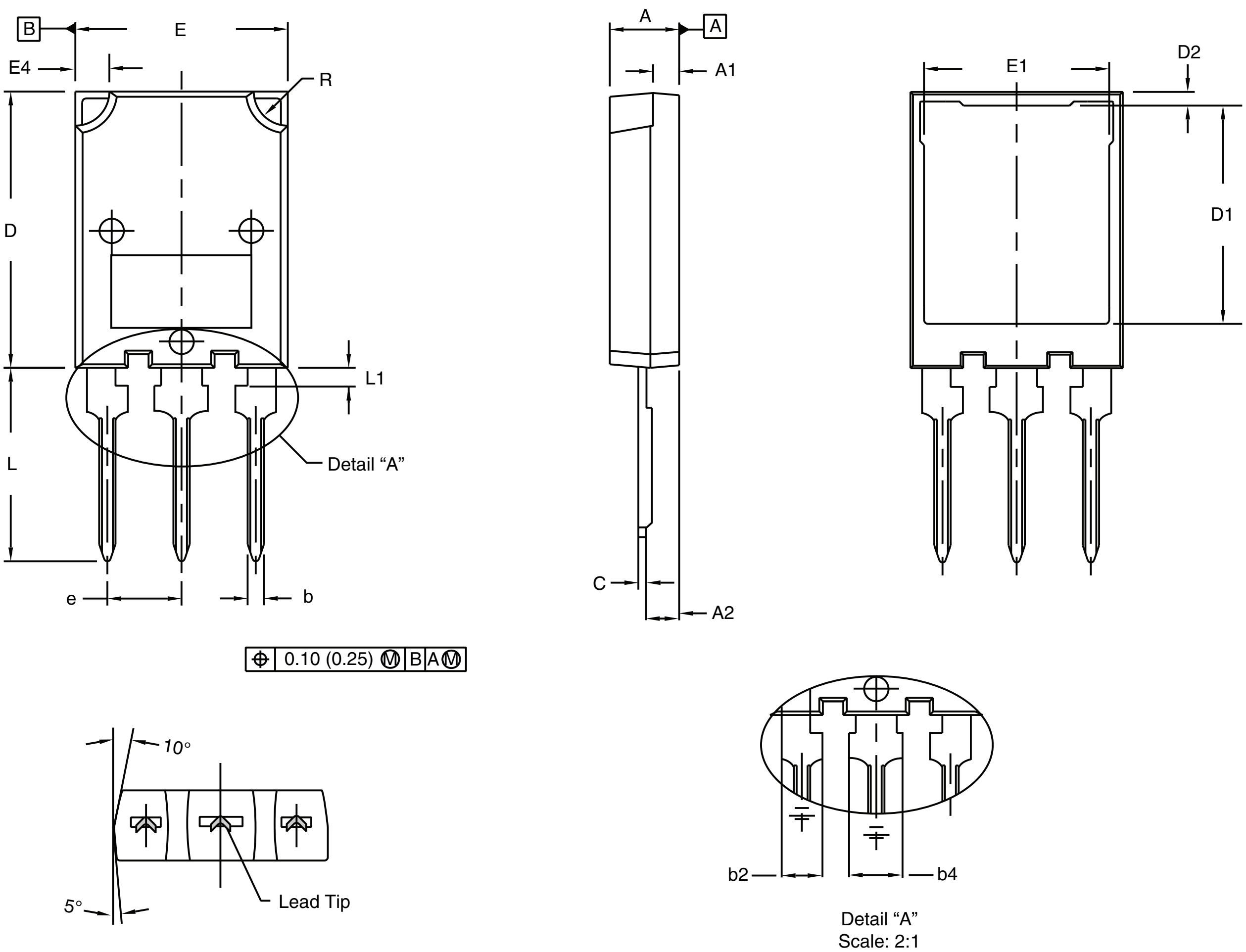
a. V_{GS} = 5 V for logic level devices

Fig. 18 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91514.

TO-274AA (High Voltage)

VERSION 1: FACILITY CODE = Y



DIM.	MILLIMETERS MIN.	MILLIMETERS MAX.	INCHES MIN.	INCHES MAX.
A	4.70	5.30	0.185	0.209
A1	1.50	2.50	0.059	0.098
A2	2.25	2.65	0.089	0.104
b	1.30	1.60	0.051	0.063
b2	1.80	2.20	0.071	0.087
b4	3.00	3.25	0.118	0.128
c [(1)]	0.38	0.89	0.015	0.035
D	19.80	20.80	0.780	0.819

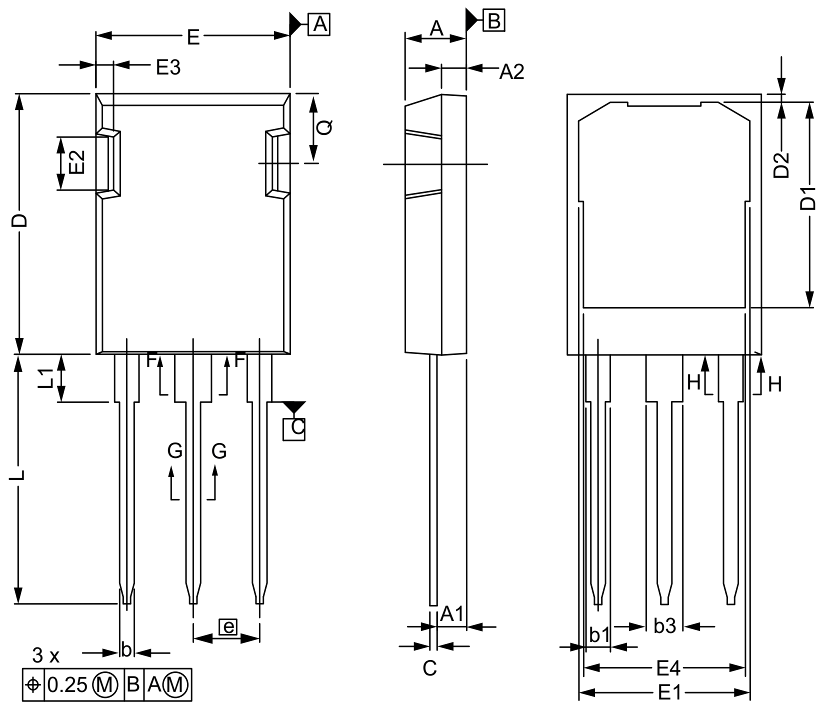
DIM.	MILLIMETERS MIN.	MILLIMETERS MAX.	INCHES MIN.	INCHES MAX.
D1	15.50	16.10	0.610	0.634
D2	0.70	1.30	0.028	0.051
E	15.10	16.10	0.594	0.634
E1	13.30	13.90	0.524	0.547
e	5.45 BSC		0.215 BSC	
L	13.70	14.70	0.539	0.579
L1	1.00	1.60	0.039	0.063
R	2.00	3.00	0.079	0.118

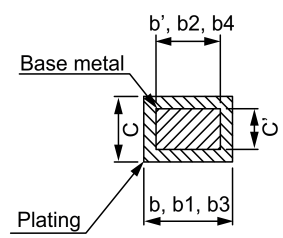
Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outer extremes of the plastic body
- Outline conforms to JEDEC® outline to TO-274AA

(1) Dimension measured at tip of lead

VERSION 2: FACILITY CODE = N





SECTION "F-F", "G-G" AND "H-H"
SCALE: NONE

	MILLIMETERS	
DIM.	**MIN.**	**MAX.**
A	4.83	5.21
A1	2.29	2.54
A2	1.91	2.16
b’	1.07	1.28
b	1.07	1.33
b1	1.91	2.41
b2	1.91	2.16
b3	2.87	3.38
b4	2.87	3.13
c’	0.55	0.65
c	0.55	0.68
D	20.80	21.10

	MILLIMETERS	
DIM.	**MIN.**	**MAX.**
D1	16.25	17.65
D2	0.50	0.80
E	15.75	16.13
E1	13.10	14.15
E2	3.68	5.10
E3	1.00	1.90
E4	12.38	13.43
e	5.44 BSC	
N	3	
L	19.81	20.32
L1	3.70	4.00
Q	5.49	6.00

ECN: E20-0538-Rev. C, 19-Oct-2020
DWG: 5975

Notes
- Dimensioning and tolerancing per ASME Y14.5M-1994
- Outline conforms to JEDEC® outline to TO-274AD
- Dimensions are measured in mm, angles are in degree
- Metal surfaces are tin plated, except area of cut

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